

IN THE CLAIMS:

Please cancel claims 1-2 and 5-6 without prejudice or disclaimer. Please amend claims 3-4 and 7-8 as follows.

Claims 1-2 (Canceled).

Claim 3 (Amended): A method of forming an interlayer dielectric film in a semiconductor device, the method comprising the steps of:
forming a conductive layer ~~patterns of a given pattern~~ and an insulating film spacer on ~~the sidewalls~~ a sidewall of said conductive layer ~~patterns~~ pattern through a common process;
removing said insulating film spacer ~~formed~~ in a region other than a contact plug formation region ~~where a contact plug will be formed~~; and
forming an interlayer dielectric film on ~~the~~ an entire surface of the semiconductor device.

Claim 4 (Currently Amended): The method ~~of forming an interlayer dielectric film in a semiconductor device as claimed in~~ according to claim 3, wherein said conductive layer ~~patterns~~ are pattern comprises one of a word lines or line and a bit lines line.

Claims 5-6 (Canceled).

Claim 7 (Currently Amended): A method of forming an interlayer dielectric film in a semiconductor device, the method comprising the steps of:

forming conductive layer patterns ~~of a given pattern~~ and an insulating film spacer on ~~the~~
a sidewall of said conductive layer patterns through a common process;

burying a conductive material between said conductive layer patterns;

removing said conductive material ~~only~~ at a given removal region ~~and remaining such~~
that said conductive material remains at remaining regions to form a contact plug; and

burying an interlayer dielectric film between said conductive layer patterns at a said
removal region ~~from which said conductive material is removed~~.

Claim 8 (Currently Amended): The method ~~of forming an interlayer dielectric film in a~~
~~semiconductor device as claimed in~~ according to claim 7, wherein at least one of said conductive
layer patterns ~~are~~ comprises one of a word lines or line and a bit lines line.